

# NX3V1T66

## Low-ohmic single-pole single-throw analog switch

Rev. 7 — 2 November 2011

Product data sheet

### 1. General description

The NX3V1T66 is a low-ohmic single-pole single-throw analog switch. It has two input/output terminals (Y and Z) and an active HIGH enable input pin (E). When pin E is LOW, the analog switch is turned off.

Schmitt trigger action at the enable input (E) makes the circuit tolerant to slower input rise and fall times. A low input voltage threshold allows pin E to be driven by lower level logic signals without a significant increase in supply current  $I_{CC}$ . This makes it possible for the NX3V1T66 to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation.

The NX3V1T66 allows signals with amplitude up to  $V_{CC}$  to be transmitted from Y to Z or from Z to Y. Its ultra-low ON resistance (0.3  $\Omega$ ) and flatness (0.1  $\Omega$ ) ensures minimal attenuation and distortion of transmitted signals.

### 2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance (peak):
  - ◆ 0.8  $\Omega$  (typical) at  $V_{CC} = 1.4$  V
  - ◆ 0.5  $\Omega$  (typical) at  $V_{CC} = 1.65$  V
  - ◆ 0.3  $\Omega$  (typical) at  $V_{CC} = 2.3$  V
  - ◆ 0.25  $\Omega$  (typical) at  $V_{CC} = 2.7$  V
  - ◆ 0.25  $\Omega$  (typical) at  $V_{CC} = 4.3$  V
- High noise immunity
- ESD protection:
  - ◆ HBM JESD22-A114F Class 3A exceeds 7500 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
  - ◆ IEC61000-4-2 contact discharge exceeds 6000 V for switch ports
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- Enable input accepts voltages above supply voltage
- 1.8 V control logic at  $V_{CC} = 3.6$  V
- High current handling capability (500 mA continuous current under 3.3 V supply)
- Specified from  $-40$  °C to  $+85$  °C and from  $-40$  °C to  $+125$  °C



3. Applications

- Cell phone
- PDA
- Portable media player

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NX3V1T66GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
NX3V1T66GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886

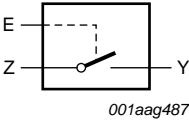
5. Marking

Table 2. Marking codes<sup>[1]</sup>

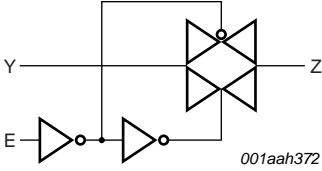
Type number	Marking code
NX3V1T66GW	dO
NX3V1T66GM	dO

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram



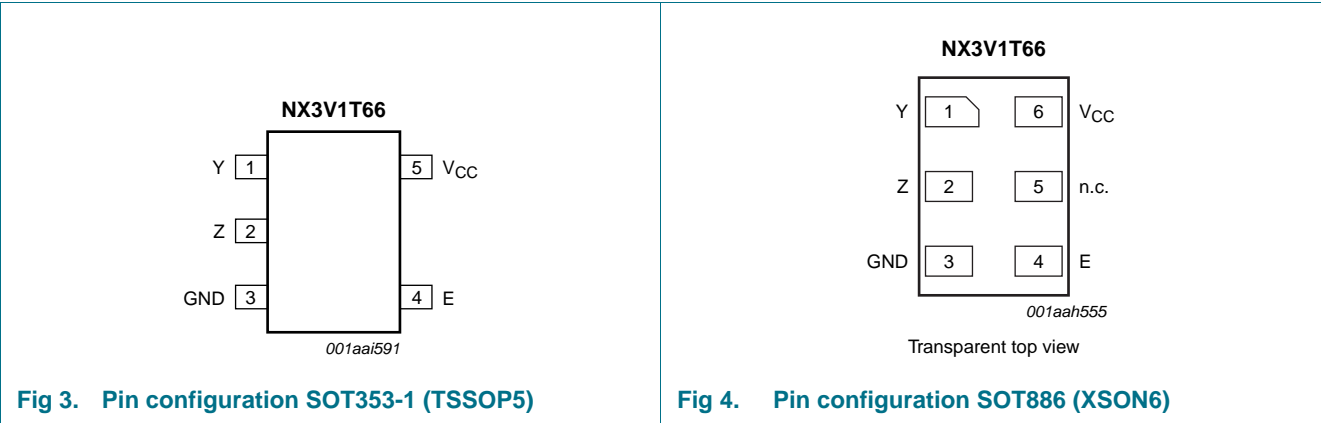
**Fig 1. Logic symbol**



**Fig 2. Logic diagram**

7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1	SOT886	
Y	1	1	independent input or output
Z	2	2	independent output or input
GND	3	3	ground (0 V)
E	4	4	enable input (active HIGH)
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

8. Functional description

Table 4. Function table<sup>[1]</sup>

Input E	Switch
L	OFF-state
H	ON-state

[1] H = HIGH voltage level; L = LOW voltage level.

## 9. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$V_I$	input voltage	enable input E	[1] -0.5	+4.6	V
$V_{SW}$	switch voltage		[2] -0.5	$V_{CC} + 0.5$	V
$I_{IK}$	input clamping current	$V_I < -0.5$ V	-50	-	mA
$I_{SK}$	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	$\pm 50$	mA
$I_{SW}$	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; source or sink current	-	$\pm 500$	mA
		$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	$\pm 750$	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

[3] For TSSOP5 package: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
For XSON6 package: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 10. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.4	4.3	V
$V_I$	input voltage	enable input E	0	4.3	V
$V_{SW}$	switch voltage		[1] 0	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.4$ V to 4.3 V	[2] -	200	ns/V

[1] To avoid sinking GND current from of terminal Z when switch current flows in terminal Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Y. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

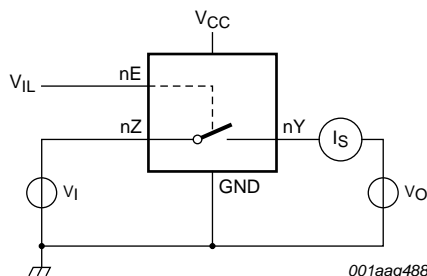
## 11. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

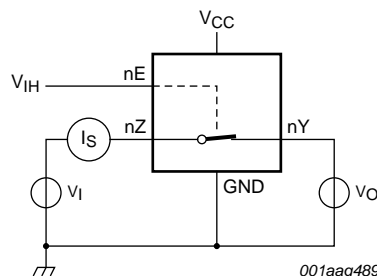
Symbol	Parameter	Conditions	T <sub>amb</sub> = 25 °C			T <sub>amb</sub> = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.4 V to 1.6 V	0.9	-	-	0.9	-	-	V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.9	-	-	0.9	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.1	-	-	1.1	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	1.3	-	-	1.3	-	-	V
		V <sub>CC</sub> = 3.6 V to 4.3 V	1.4	-	-	1.4	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.4 V to 1.6 V	-	-	0.3	-	0.3	0.3	V
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.4	-	0.4	0.3	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.4	-	0.4	0.4	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.5	-	0.5	0.5	V
		V <sub>CC</sub> = 3.6 V to 4.3 V	-	-	0.6	-	0.6	0.6	V
I <sub>I</sub>	input leakage current	enable input E; V <sub>I</sub> = GND to 4.3 V; V <sub>CC</sub> = 1.4 V to 4.3 V							
I <sub>S(OFF)</sub>	OFF-state leakage current	Y port; see <a href="#">Figure 5</a>							
		V <sub>CC</sub> = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V <sub>CC</sub> = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I <sub>S(ON)</sub>	ON-state leakage current	Z port; see <a href="#">Figure 6</a>							
		V <sub>CC</sub> = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V <sub>CC</sub> = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 3.6 V; V <sub>SW</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A							
		V <sub>CC</sub> = 3.6 V	-	-	100	-	690	6000	nA
		V <sub>CC</sub> = 4.3 V	-	-	150	-	800	7000	nA
ΔI <sub>CC</sub>	additional supply current	V <sub>SW</sub> = GND or V <sub>CC</sub>							
		V <sub>I</sub> = 2.6 V; V <sub>CC</sub> = 4.3 V	-	2.0	4.0	-	7	7	μA
		V <sub>I</sub> = 2.6 V; V <sub>CC</sub> = 3.6 V	-	0.35	0.7	-	1	1	μA
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 4.3 V	-	7.0	10.0	-	15	15	μA
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 3.6 V	-	2.5	4.0	-	5	5	μA
		V <sub>I</sub> = 1.8 V; V <sub>CC</sub> = 2.5 V	-	50	200	-	300	500	nA
C <sub>I</sub>	input capacitance		-	1.0	-	-	-	-	pF
C <sub>S(OFF)</sub>	OFF-state capacitance		-	70	-	-	-	-	pF
C <sub>S(ON)</sub>	ON-state capacitance		-	205	-	-	-	-	pF

## 11.1 Test circuits



$V_I = 0.3 \text{ V}$  or  $V_{CC} - 0.3 \text{ V}$ ;  $V_O = V_{CC} - 0.3 \text{ V}$  or  $0.3 \text{ V}$ .

**Fig 5. Test circuit for measuring OFF-state leakage current**



$V_I = 0.3 \text{ V}$  or  $V_{CC} - 0.3 \text{ V}$ ;  $V_O = \text{open circuit}$ .

**Fig 6. Test circuit for measuring ON-state leakage current**

## 11.2 ON resistance

**Table 8. Resistance  $R_{ON}$**

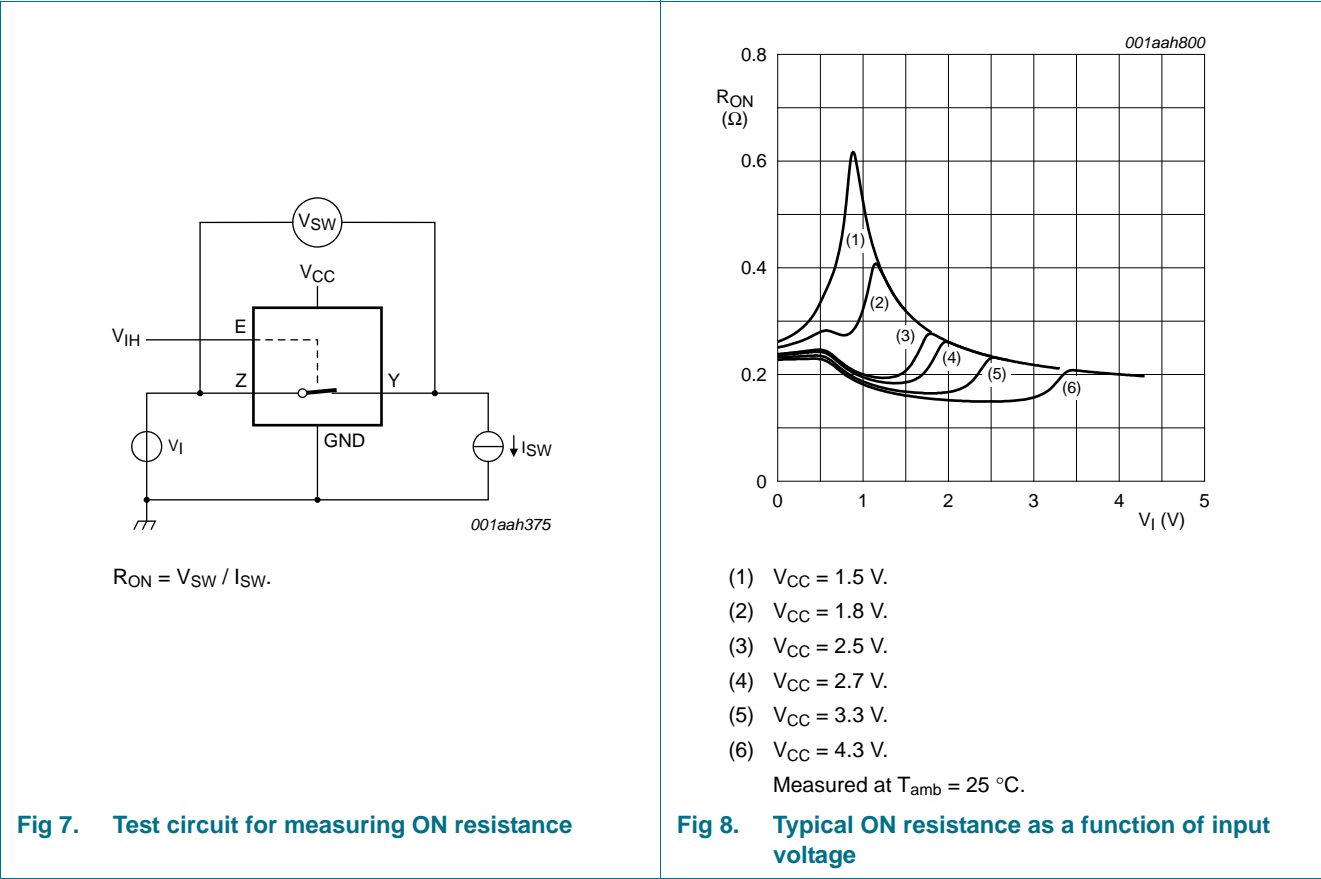
At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 8](#) to [Figure 14](#).

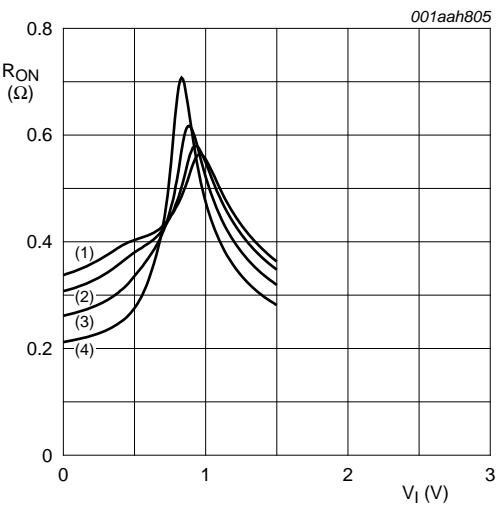
Symbol	Parameter	Conditions	$T_{amb} = -40 \text{ }^{\circ}\text{C}$ to $+85 \text{ }^{\circ}\text{C}$			$T_{amb} = -40 \text{ }^{\circ}\text{C}$ to $+125 \text{ }^{\circ}\text{C}$		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
$R_{ON(peak)}$	ON resistance (peak)	$V_I = \text{GND to } V_{CC}$ ; $I_{SW} = 100 \text{ mA}$ ; see <a href="#">Figure 7</a>						
		$V_{CC} = 1.4 \text{ V}$	-	0.8	1.9	-	2.1	$\Omega$
		$V_{CC} = 1.65 \text{ V}$	-	0.5	0.8	-	0.9	$\Omega$
		$V_{CC} = 2.3 \text{ V}$	-	0.3	0.5	-	0.6	$\Omega$
		$V_{CC} = 2.7 \text{ V}$	-	0.25	0.45	-	0.5	$\Omega$
		$V_{CC} = 4.3 \text{ V}$	-	0.25	0.45	-	0.5	$\Omega$
$R_{ON(flat)}$	ON resistance (flatness)	$V_I = \text{GND to } V_{CC}$ ; $I_{SW} = 100 \text{ mA}$ <a href="#">[2]</a>						
		$V_{CC} = 1.4 \text{ V}$	-	0.5	1.7	-	1.8	$\Omega$
		$V_{CC} = 1.65 \text{ V}$	-	0.25	0.6	-	0.7	$\Omega$
		$V_{CC} = 2.3 \text{ V}$	-	0.1	0.2	-	0.2	$\Omega$
		$V_{CC} = 2.7 \text{ V}$	-	0.1	0.2	-	0.2	$\Omega$
		$V_{CC} = 4.3 \text{ V}$	-	0.1	0.25	-	0.25	$\Omega$

[1] Typical values are measured at  $T_{amb} = 25 \text{ }^{\circ}\text{C}$ .

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical  $V_{CC}$  and temperature.

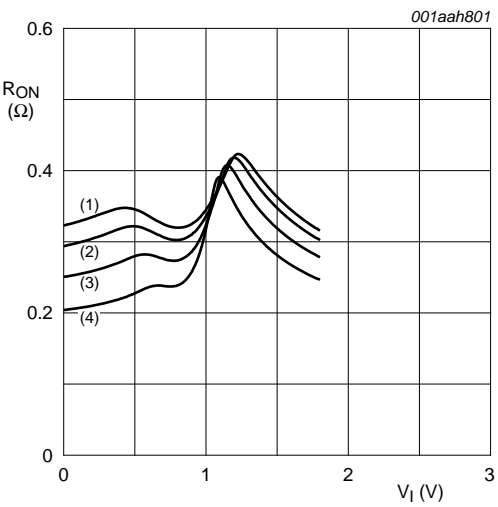
11.3 ON resistance test circuit and graphs





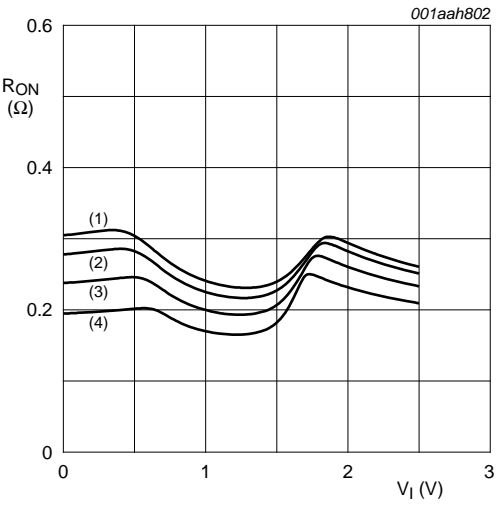
- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 9. ON resistance as a function of input voltage;  
 $V_{CC} = 1.5\text{ V}$



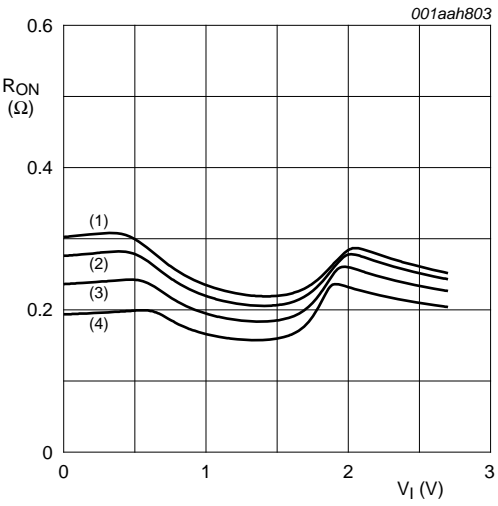
- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 10. ON resistance as a function of input voltage;  
 $V_{CC} = 1.8\text{ V}$



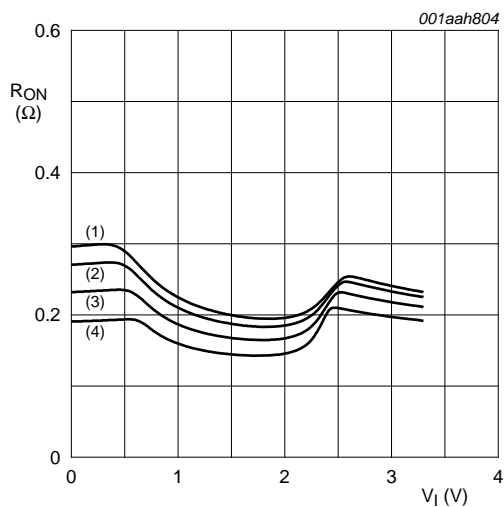
- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage;  
 $V_{CC} = 2.5\text{ V}$



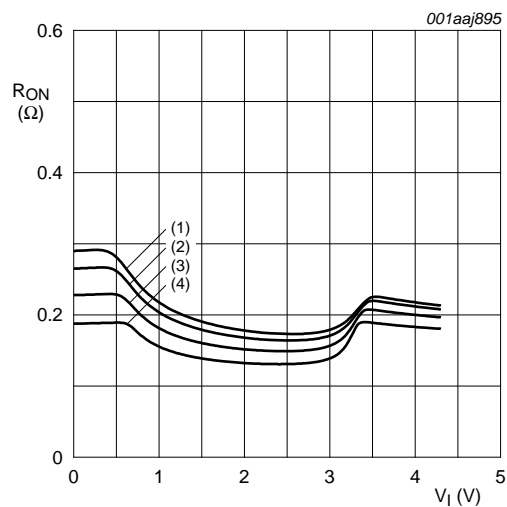
- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 12. ON resistance as a function of input voltage;  
 $V_{CC} = 2.7\text{ V}$



- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}$ .
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}$ .
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}$ .

**Fig 13. ON resistance as a function of input voltage;**  
 $V_{CC} = 3.3\text{ V}$



- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}$ .
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}$ .
- (3)  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .
- (4)  $T_{amb} = -40\text{ }^{\circ}\text{C}$ .

**Fig 14. ON resistance as a function of input voltage;**  
 $V_{CC} = 4.3\text{ V}$

## 12. Dynamic characteristics

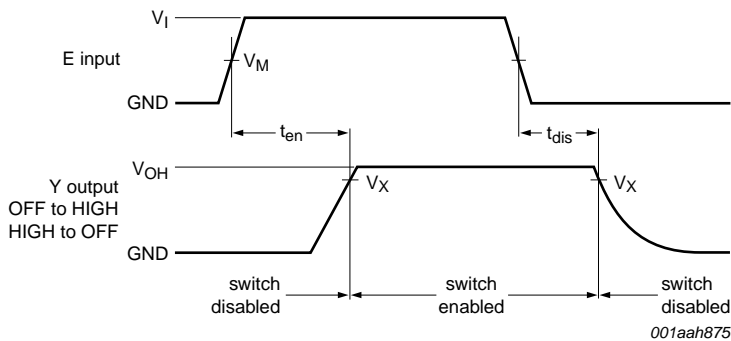
**Table 9. Dynamic characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit [Figure 16](#).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ }^{\circ}\text{C}$			$T_{amb} = -40\text{ }^{\circ}\text{C to } +125\text{ }^{\circ}\text{C}$			Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max (85 °C)	Max (125 °C)	
$t_{en}$	enable time	E to Y; see <a href="#">Figure 15</a>							
		$V_{CC} = 1.4\text{ V to } 1.6\text{ V}$	-	35	49	-	53	57	ns
		$V_{CC} = 1.65\text{ V to } 1.95\text{ V}$	-	28	40	-	43	48	ns
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	-	20	30	-	32	35	ns
		$V_{CC} = 2.7\text{ V to } 3.6\text{ V}$	-	18	28	-	30	32	ns
		$V_{CC} = 3.6\text{ V to } 4.3\text{ V}$	-	18	28	-	30	32	ns
$t_{dis}$	disable time	E to Y; see <a href="#">Figure 15</a>							
		$V_{CC} = 1.4\text{ V to } 1.6\text{ V}$	-	32	70	-	80	90	ns
		$V_{CC} = 1.65\text{ V to } 1.95\text{ V}$	-	23	55	-	60	65	ns
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	-	14	25	-	30	35	ns
		$V_{CC} = 2.7\text{ V to } 3.6\text{ V}$	-	11	20	-	25	30	ns
		$V_{CC} = 3.6\text{ V to } 4.3\text{ V}$	-	11	20	-	25	30	ns

[1] Typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$  and  $V_{CC} = 1.5\text{ V, } 1.8\text{ V, } 2.5\text{ V, } 3.3\text{ V}$  and  $4.3\text{ V}$  respectively.

12.1 Waveform and test circuits

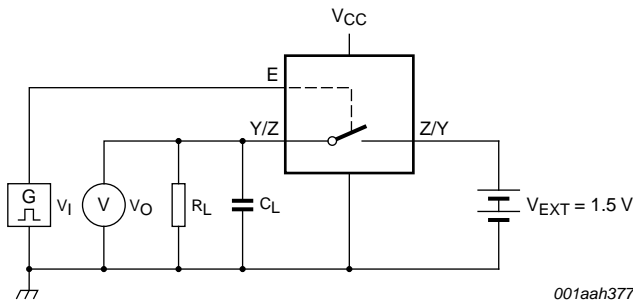


Measurement points are given in [Table 10](#).  
Logic level:  $V_{OH}$  is the typical output voltage that occurs with the output load.

Fig 15. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output
$V_{CC}$	$V_M$	$V_X$
1.4 V to 4.3 V	$0.5V_{CC}$	$0.9V_{OH}$



Test data is given in [Table 11](#).  
Definitions test circuit:  
 $R_L$  = Load resistance.  
 $C_L$  = Load capacitance including jig and probe capacitance.  
 $V_{EXT}$  = External voltage for measuring switching times.

Fig 16. Load circuit for switching times

Table 11. Test data

Supply voltage	Input		Load	
$V_{CC}$	$V_I$	$t_r, t_f$	$C_L$	$R_L$
1.4 V to 4.3 V	$V_{CC}$	$\leq 2.5 \text{ ns}$	35 pF	50 $\Omega$

## 12.2 Additional dynamic characteristics

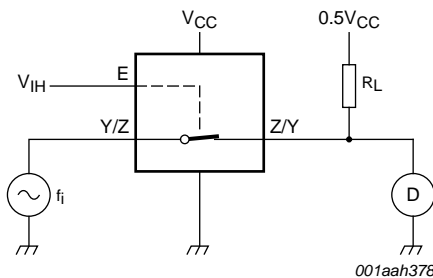
**Table 12. Additional dynamic characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $V_I = \text{GND}$  or  $V_{CC}$  (unless otherwise specified);  $t_r = t_f \leq 2.5 \text{ ns}$ ;  $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$ .

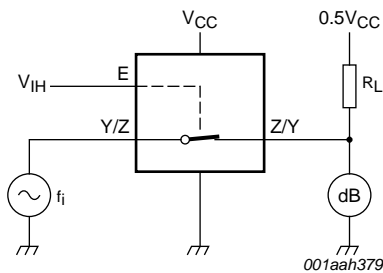
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$f_i = 20 \text{ Hz to } 20 \text{ kHz}$ ; $R_L = 32 \text{ } \Omega$ ; see <a href="#">Figure 17</a>	[1]			
		$V_{CC} = 1.4 \text{ V}$ ; $V_I = 1 \text{ V (p-p)}$	-	0.05	-	%
		$V_{CC} = 1.65 \text{ V}$ ; $V_I = 1.2 \text{ V (p-p)}$	-	0.03	-	%
		$V_{CC} = 2.3 \text{ V}$ ; $V_I = 1.5 \text{ V (p-p)}$	-	0.01	-	%
		$V_{CC} = 2.7 \text{ V}$ ; $V_I = 2 \text{ V (p-p)}$	-	0.01	-	%
$f_{(-3\text{dB})}$	–3 dB frequency response	$R_L = 50 \text{ } \Omega$ ; see <a href="#">Figure 18</a>	[1]			
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	25	-	MHz
$\alpha_{\text{iso}}$	isolation (OFF-state)	$f_i = 100 \text{ kHz}$ ; $R_L = 50 \text{ } \Omega$ ; see <a href="#">Figure 19</a>	[1]			
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	–90	-	dB
$V_{\text{ct}}$	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}$ ; $C_L = 50 \text{ pF}$ ; $R_L = 50 \text{ } \Omega$ ; see <a href="#">Figure 20</a>				
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	0.3	-	V
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	0.5	-	V
$Q_{\text{inj}}$	charge injection	$f_i = 1 \text{ MHz}$ ; $C_L = 0.1 \text{ nF}$ ; $R_L = 1 \text{ M}\Omega$ ; $V_{\text{gen}} = 0 \text{ V}$ ; $R_{\text{gen}} = 0 \text{ } \Omega$ ; see <a href="#">Figure 21</a>				
		$V_{CC} = 1.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 1.8 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 2.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 4.3 \text{ V}$	-	12	-	pC

[1]  $f_i$  is biased at  $0.5V_{CC}$ .

## 12.3 Test circuits

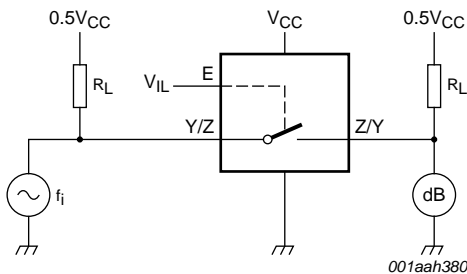


**Fig 17. Test circuit for measuring total harmonic distortion**



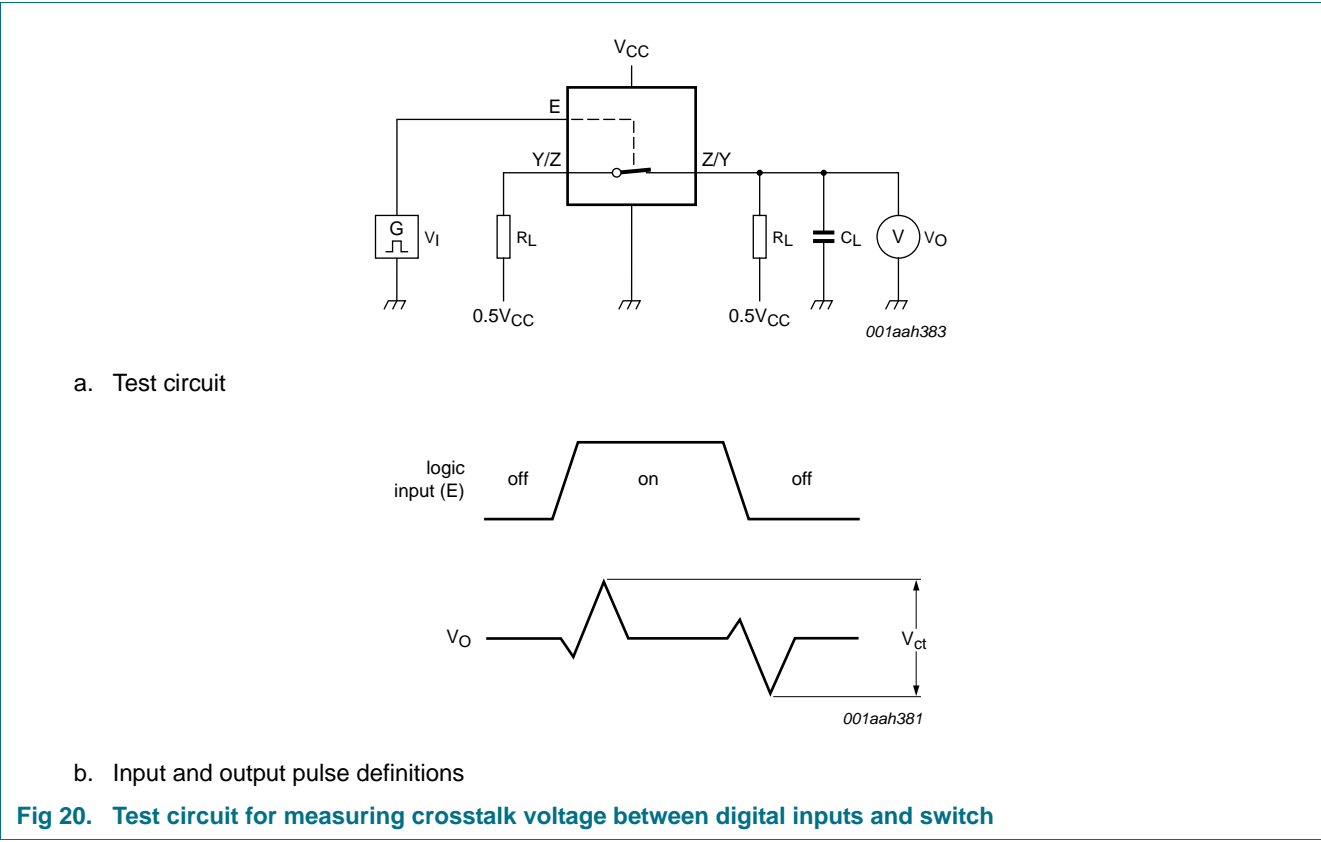
Adjust  $f_i$  voltage to obtain 0 dBm level at output. Increase  $f_i$  frequency until dB meter reads  $-3$  dB.

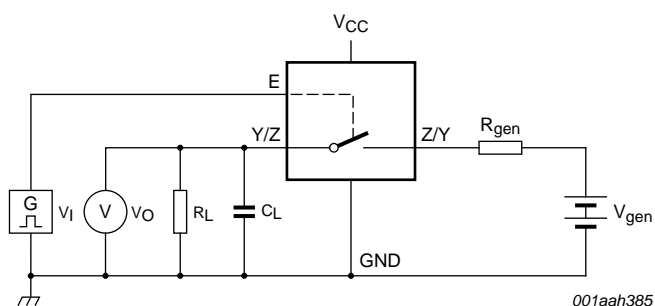
**Fig 18. Test circuit for measuring the frequency response when channel is in ON-state**



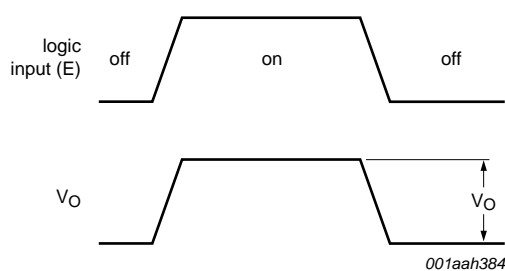
Adjust  $f_i$  voltage to obtain 0 dBm level at input.

**Fig 19. Test circuit for measuring isolation (OFF-state)**





a. Test circuit



b. Input and output pulse definitions

Definition:  $Q_{inj} = \Delta V_O \times C_L$ .

$\Delta V_O$  = output voltage variation.

$R_{gen}$  = generator resistance.

$V_{gen}$  = generator voltage.

**Fig 21. Test circuit for measuring charge injection**

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

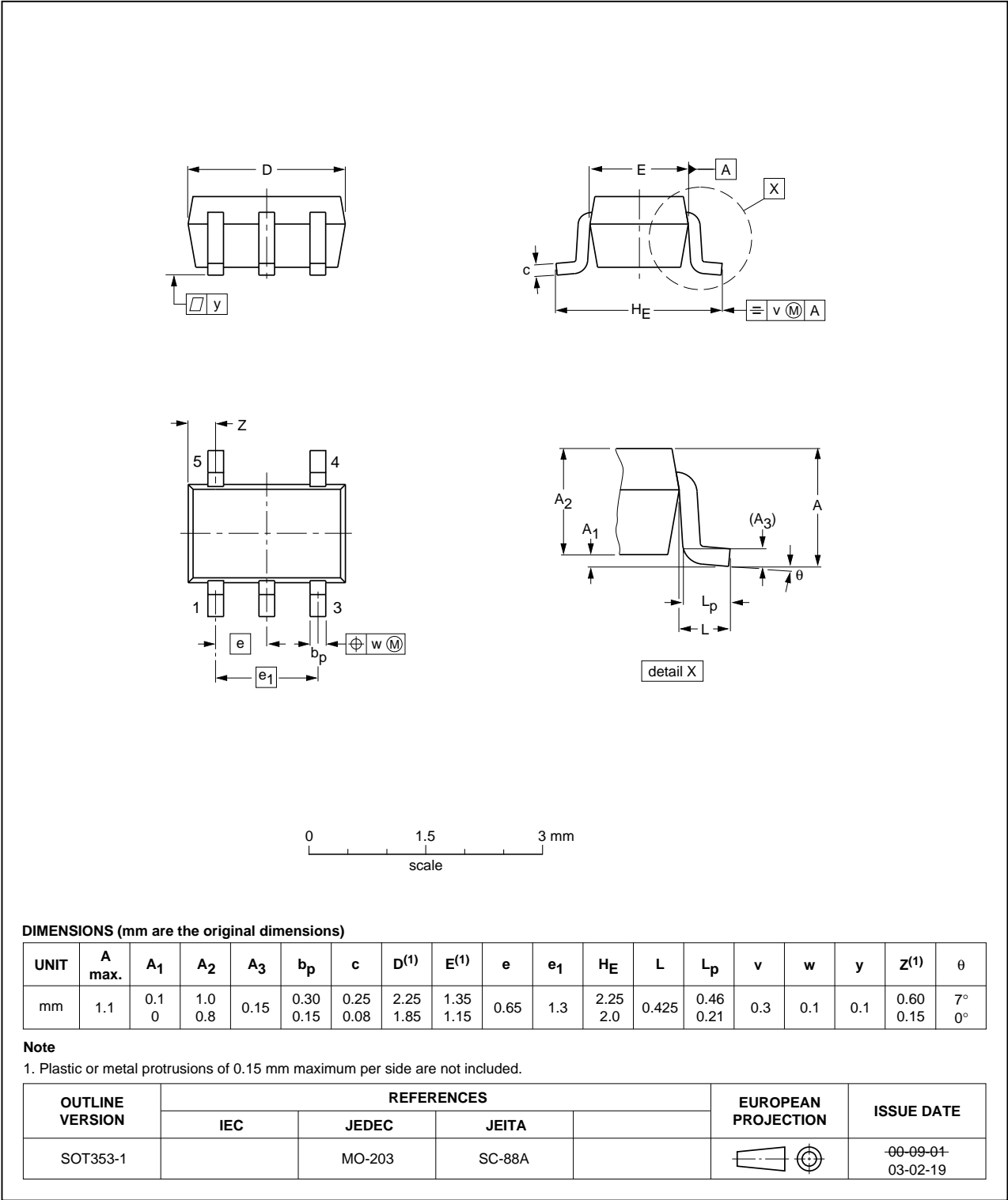


Fig 22. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

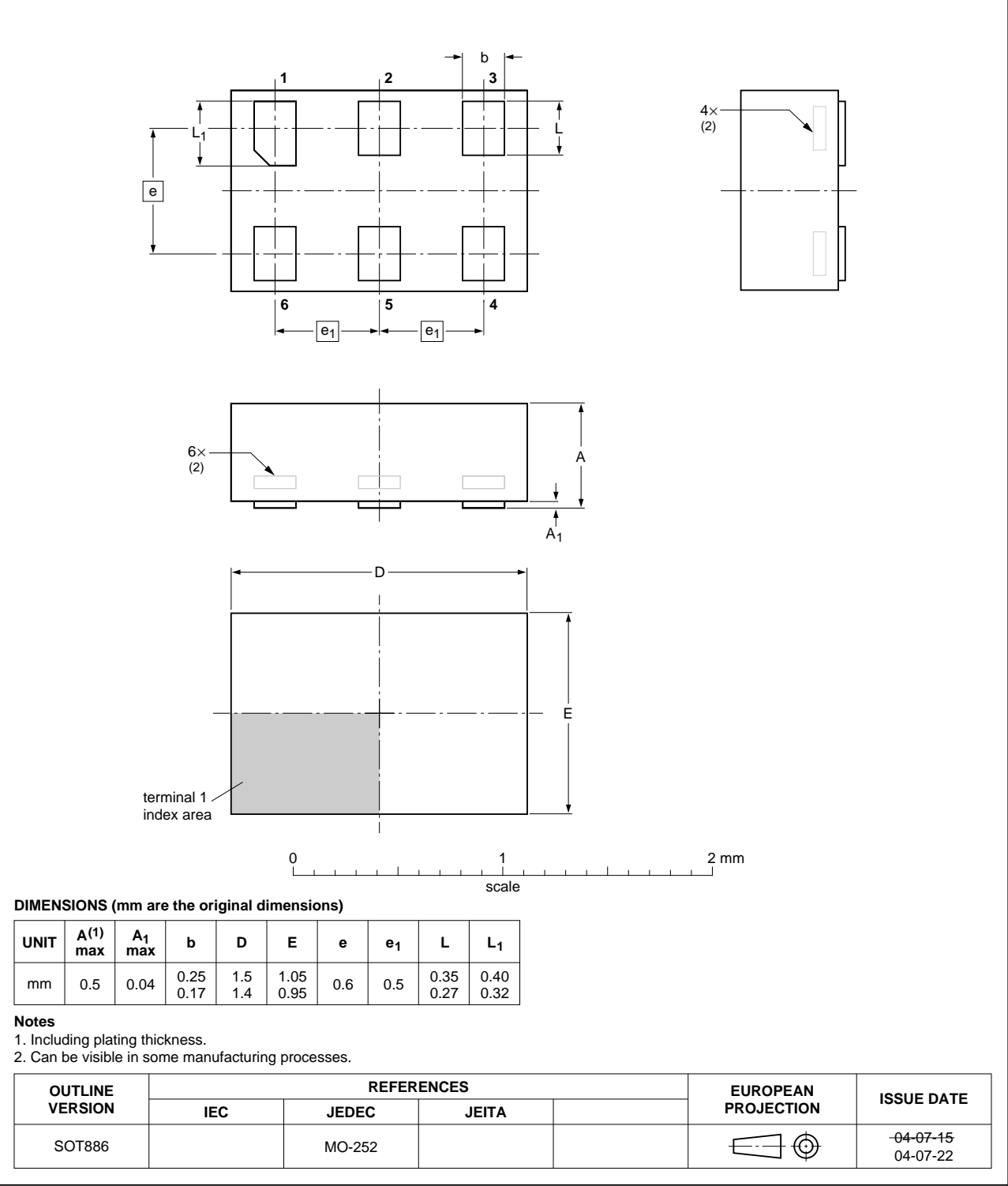


Fig 23. Package outline SOT886 (XSON6)

## 14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PDA	Personal Digital Assistant

## 15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3V1T66 v.7	20111102	Product data sheet	-	NX3V1T66 v.6
Modifications:	• Legal pages updated			
NX3V1T66 v.6	20101221	Product data sheet	-	NX3V1T66 v.5
NX3V1T66 v.5	20100324	Product data sheet	-	NX3V1T66 v.4
NX3V1T66 v.4	20100202	Product data sheet	-	NX3V1T66 v.3
NX3V1T66 v.3	20090504	Product data sheet	-	NX3V1T66 v.2
NX3V1T66 v.2	20080724	Product data sheet	-	NX3V1T66 v.1
NX3V1T66 v.1	20080327	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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